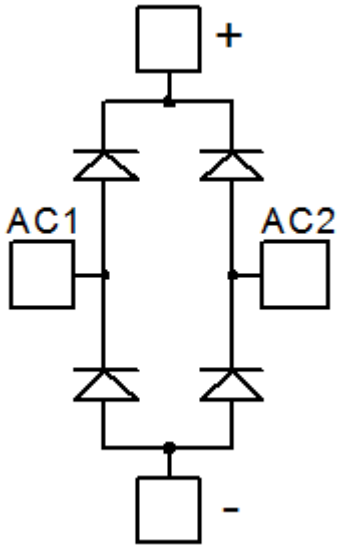
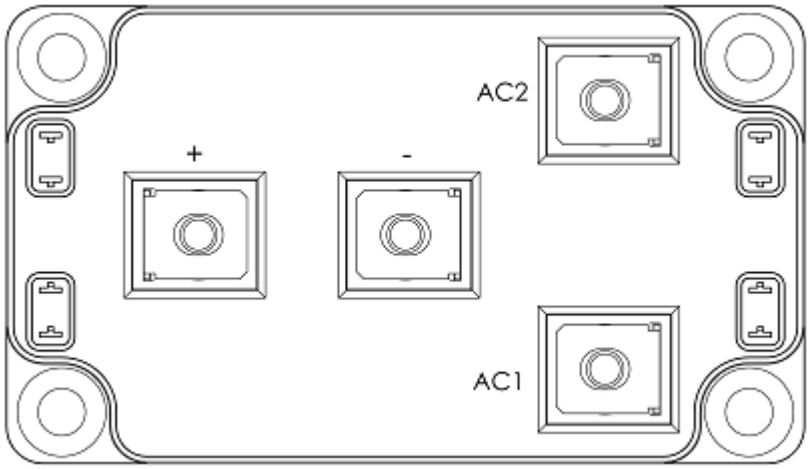
MSCDC100H70AG SiC Diode Full Bridge Power Module

1 Product Overview

This section shows the product overview of the MSCDC100H70AG device.





All ratings at T_j = 25 °C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

1.1 Features

The following are key features of the MSCDC100H70AG device:

- Silicon carbide (SiC) Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature-independent switching behavior
  - Positive temperature coefficient on VF
- High blocking voltage
- Low stray inductance
- M5 power connectors
- Aluminum nitride (AlN) substrate for improved thermal performance

1.2 Benefits

The following are benefits of the MSCDC100H70AG device:

- Outstanding performance at high-frequency operation
- Low losses
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS compliant

1.3 Applications

The MSCDC100H70AG device is designed for the following applications:

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

2 Electrical Specifications

This section shows the electrical specifications of the MSCDC100H70AG device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode of the MSCDC100H70AG device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
V_{RRM}	Repetitive peak reverse voltage		700	V
I_F	DC forward current	T_C = 70 °C	100	A

The following table shows the thermal and package characteristics of the MSCDC100H70AG device.

Table 2 • Thermal and Package Characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz			4000		V
T_J	Operating junction temperature range			–40	175	°C
T_{JOP}	Recommended junction temperature under switching conditions			–40	T_{Jmax}–25	
T_{STG}	Storage temperature range			–40	125	
T_C	Operating case temperature			–40	125	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package weight				300	g

2.2 Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSCDC100H70AG device.

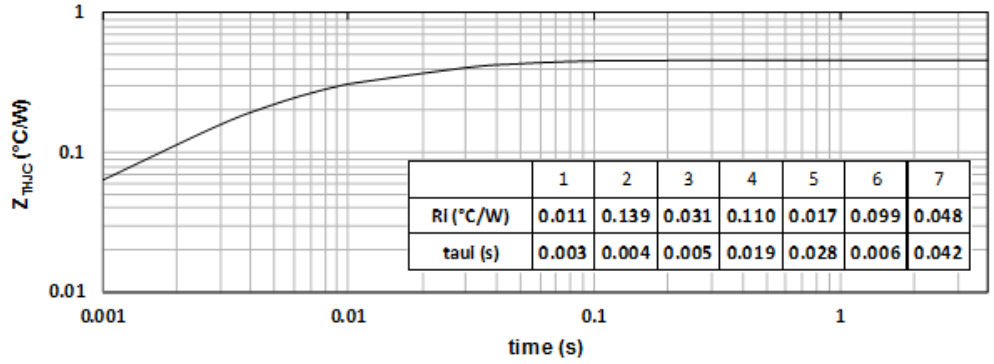
Table 3 • Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_F	Diode forward voltage	I_F = 100 A	T_j = 25 °C		1.5	1.8	V
			T_j = 175 °C		1.9		
I_{RM}	Reverse leakage current	V_R = 700 V	T_j = 25 °C		30	400	µA
			T_j = 175 °C		500		
Q_C	Total capacitive charge	V_R = 400 V			266		nC
C	Total capacitance	f = 1 MHz, V_R = 200 V			496		pF
		f = 1 MHz, V_R = 400 V			432		
R_{thJC}	Junction-to-case thermal resistance					0.456	°C/W

2.3 Typical Performance Curves

This section shows the typical performance curves of the MSCDC100H70AG device.

Figure 1 • Maximum Transient Thermal Impedance



	1	2	3	4	5	6	7
RI (°C/W)	0.011	0.139	0.031	0.110	0.017	0.099	0.048
taul (s)	0.003	0.004	0.005	0.019	0.028	0.006	0.042

Figure 2 • Forward Current vs. Forward Voltage

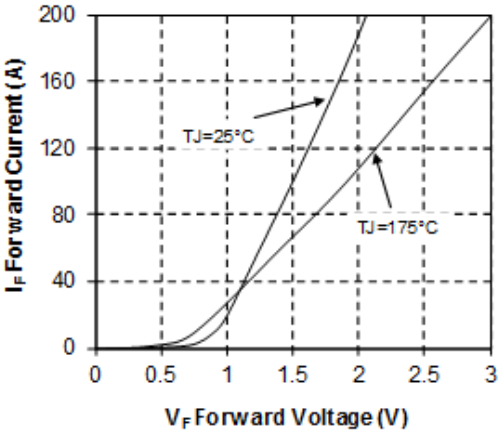
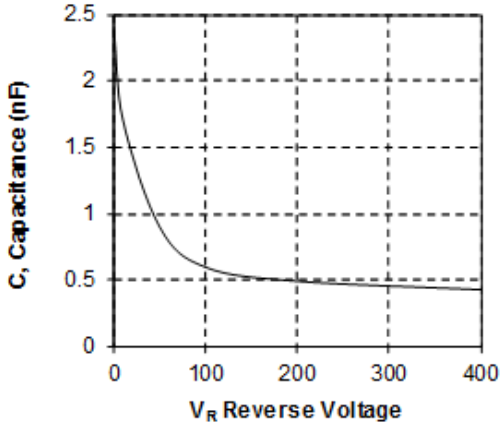


Figure 3 • Capacitance vs. Reverse Voltage



3 Package Specification

This section shows the package specifications for the MSCDC100H70AG device.

3.1 Package Outline Drawing

The package outline of the MSCDC100H70AG device is illustrated in this section. The dimensions in the following figure are in millimeters.

Figure 4 • Package Outline Drawing